

# AG603-86

InGaP HBT Gain Block

Product Information



wj

## Product Features

- DC – 6000 MHz
- +19.5 dBm P1dB at 900 MHz
- +33.5 dBm OIP3 at 900 MHz
- 18.5 dB Gain at 900 MHz
- Single Voltage Supply
- Green SOT-86 SMT Package
- Internally matched to 50 Ω

## Applications

- Mobile Infrastructure
- CATV / DBS
- W-LAN / ISM
- RFID
- Defense / Homeland Security
- Fixed Wireless

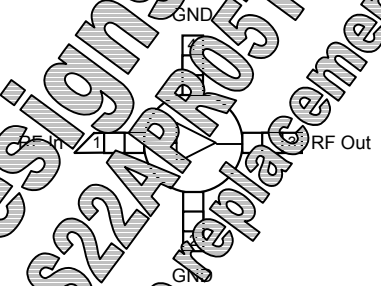
## Product Description

The AG603-86 is a general-purpose buffer amplifier that offers high dynamic range in a low-cost surface-mount package. At 900 MHz, the AG603-86 typically provides 18.5 dB gain, +33.5 dBm OIP3, and +19.5 dBm P1dB. The device combines dependable performance with consistent quality to maintain MTTF values exceeding 100 years at mounting temperatures of +85 °C & is housed in a SOT-86 industry-standard SMT lead-free/green/RoHS-compliant package.

The AG603-86 consists of Darlington pair amplifiers using the high reliability InGaP/GaAs HBT process technology and only requires DC-blocking capacitors, a resistor, and an inductive RF choke for operation.

The broadband MMIC amplifier can be directly applied to various current and next generation wireless technologies such as GPRS, GSM, CDMA, and W-CDMA. In addition, the AG603-86 will work for other various applications within the DC to 6 GHz frequency range such as CATV and fixed wireless.

## Functional Diagram



Function	Pin No.
RF In	1
Output Bias	3
Ground	2, 4

## Specifications <sup>(1)</sup>

Parameter	Units	Min	Typ	Max
Operational Bandwidth	MHz	DC		6000
Test Frequency	MHz		900	
Gain	dB		18.5	16.9
Input Return Loss	dB		20	
Output Return Loss	dB		17	
Output IP3 <sup>(2)</sup>	dBm		+33.5	
Output IP2	dBm		+33	
Output P1dB	dBm		+19.5	
Noise Figure	dB		3.8	
Test Frequency	MHz		900	
Gain	dB		18.5	16.9
Output IP3 <sup>(2)</sup>	dBm		+33.5	
Output P1dB	dBm		+19.5	
Device Voltage	V		5.16	
Device Current	mA		75	

## Typical Performance <sup>(1)</sup>

Parameter	Units	Typical			
Frequency	MHz	500	900	1900	2140
Gain	dB	18.9	18.2	15.9	15.3
Input Return Loss	dB	-17	-20	-18	-17
Output Return Loss	dB	-21	-17	-14	-13
Output P1dB	dBm	+19.4	+19.4	+19.2	+19.1
Output IP3	dBm	+34.1	+33.7	+33.4	+32.8
Noise Figure	dB	3.8	3.8	3.9	4.0

1. Test conditions: Test Frequency = 900 MHz, Supply Voltage = 5.16V, R<sub>bias</sub> = 110 Ω, 50 Ω System.  
 2. 3OIP measured with two tones at an output power of +2 dBm/tone separated by 10 MHz. The suppression of the 3IM3 products is used to calculate the 3OIP using a 2:1 rule.  
 3. The junction temperature ensures a minimum MTTF of 1 million hours of usage.

## Absolute Maximum Rating

Parameter	Rating
Operating Case Temperature	-40 to +85 °C
Storage Temperature	-55 to +125 °C
DC Voltage	+7 V
Output Power (Continuous)	+10 dBm
Maximum Temperature	+250 °C

Operation of this device above any of these parameters may cause permanent damage.

## Ordering Information

Part No.	Description
AG603-86	InGaP HBT Gain Block (lead-tin SOT-86 Pkg)
AG603-86G	InGaP HBT Gain Block (lead-free/green/RoHS-compliant SOT-86 Pkg)

Specifications and information are subject to change without notice

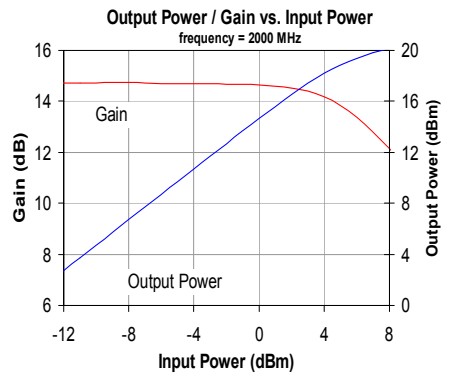
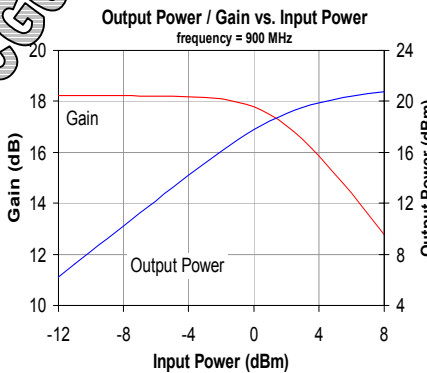
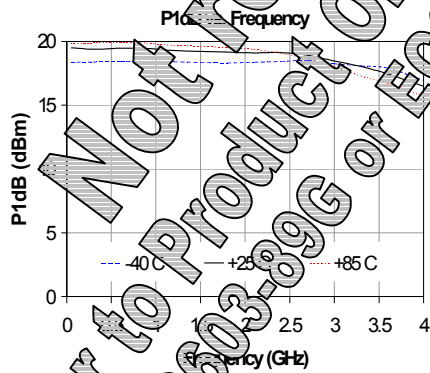
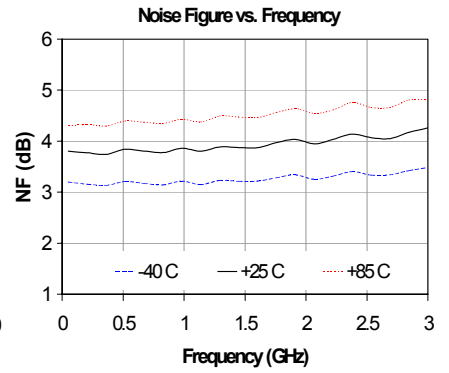
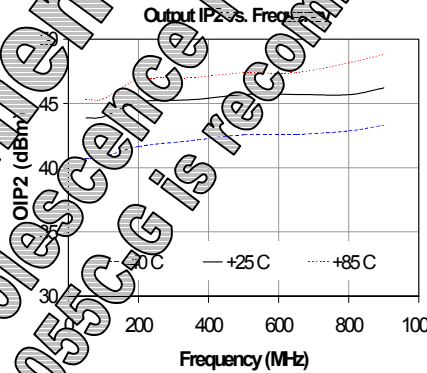
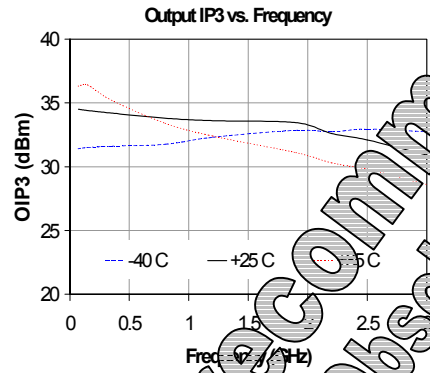
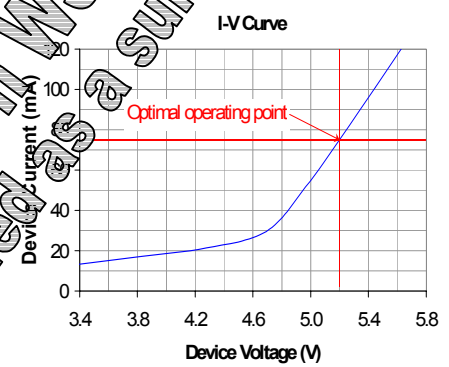
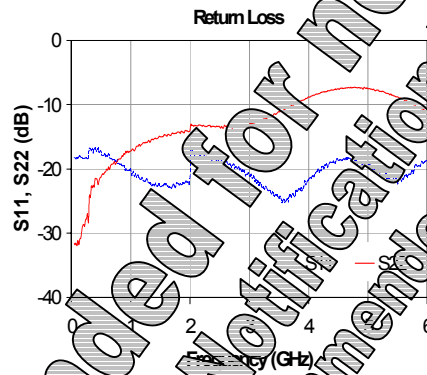
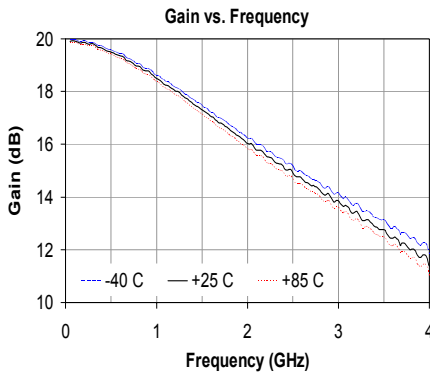


### Typical Device RF Performance

Supply Bias = +6 V,  $R_{bias} = 11.2 \Omega$ ,  $I_{cc} = 75 \text{ mA}$

Frequency	MHz	100	500	900	1900	2140	2400	3500	8000
S21	dB	19.3	18.9	18.2	15.9	15.3	14.9		
S11	dB	-18	-17	-20	-18	-17	-18		
S22	dB	-31	-21	-17	-14	-13	-13		
Output P1dB	dBm	+19.4	+19.4	+19.4	+19.2	+19.1	+19.1	+17.5	
Output IP3	dBm	+34.5	+34.1	+33.7	+33.4	+32.8			
Noise Figure	dB	3.8	3.8	3.8	3.9	4.0			

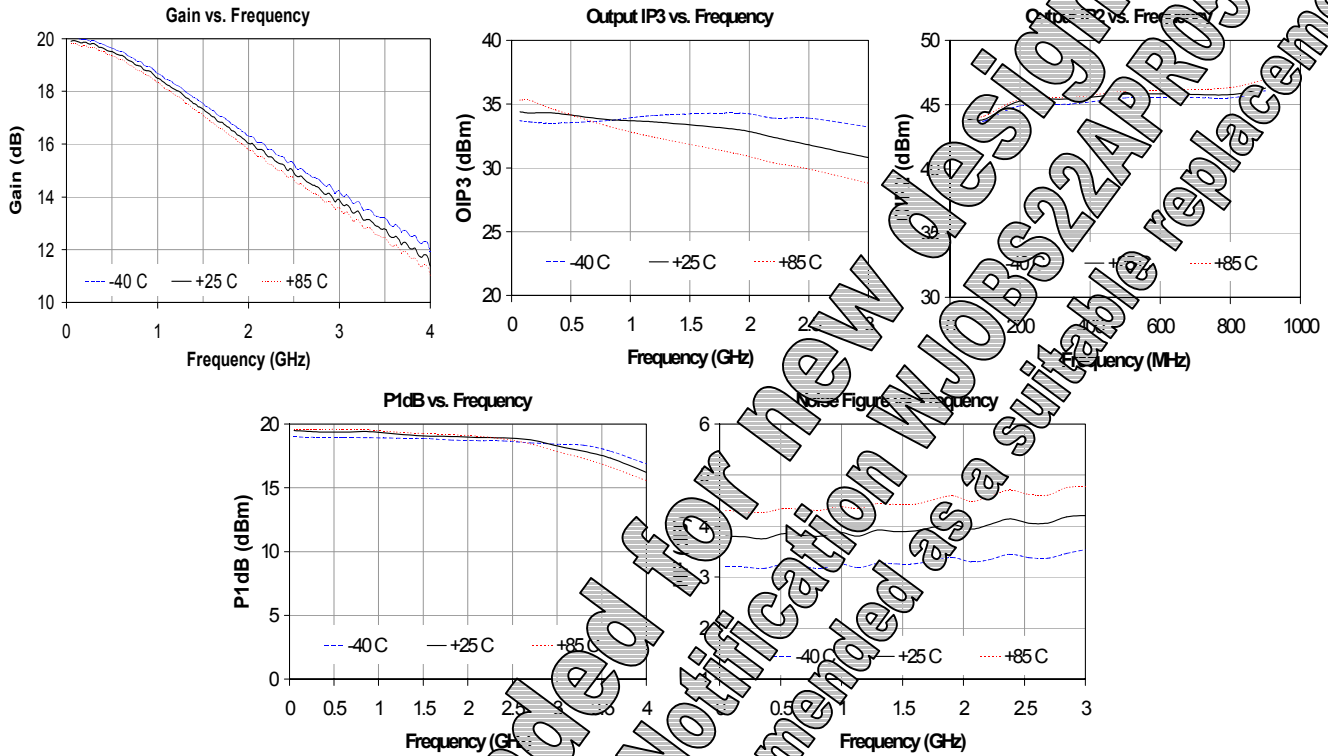
1. Test conditions: T = 25°C, Supply Voltage = +6 V, Device Voltage = 5.16 V,  $R_{bias} = 11.2 \Omega$ ,  $I_{cc} = 75 \text{ mA}$  typical, 50  $\Omega$  System
2. 3OIP measured with two tones at an output power of +2 dBm/tone separated by 10 MHz. The suppression on the largest IM3 product is used to calculate the 3OIP using the following equation.
3. Data is shown as device performance only. Actual implementation for the desired frequency band will be determined by external components shown in the application.



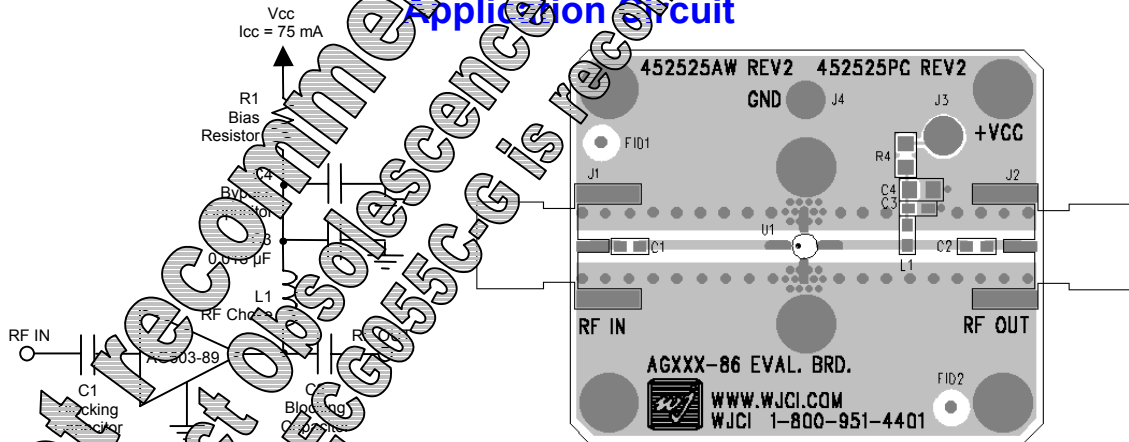


### Typical Device RF Performance (cont'd)

Supply Bias = +8 V,  $R_{bias} = 38 \Omega$ ,  $I_{cc} = 75 \text{ mA}$



### Application Circuit



#### Recommended Component Values

Reference Designator	Frequency (MHz)						
	50	100	900	1900	2200	2500	3500
L1	39 nH	39 nH	68 nH	27 nH	22 nH	18 nH	15 nH
C1, C2, C4	0.018 μF	0.018 μF	100 pF	68 pF	68 pF	56 pF	39 pF

- The proper value for the components are dependent upon the intended frequency of operation.
- The following values are guaranteed on the evaluation board to achieve optimal broadband performance:

Ref. Designator	Value / Type	Size
L1	39 nH wirewound inductor	0603
C1	56 pF chip capacitor	0603
C2	0.018 μF chip capacitor	0603
C3	Do Not Place	
R1	10.0 Ω 1% tolerance	0805

#### Recommended Bias Resistor Values

Supply Voltage	R1 value	Size
6 V	11.2 ohms	0805
7 V	24.5 ohms	1210
8 V	38 ohms	1210
9 V	51 ohms	2010
10 V	65 ohms	2010
12 V	91 ohms	2512

The proper value for R1 is dependent upon the supply voltage and allows for bias stability over temperature. WJ recommends a minimum supply bias of +6 V. A 1% tolerance resistor is recommended.

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## Typical Device Data

S-Parameters ( $V_{\text{device}} = +5.16 \text{ V}$ ,  $I_{\text{CC}} = 75 \text{ mA}$ ,  $T = 25^\circ \text{ C}$ , calibrated to device leads)

Freq (MHz)	S11 (dB)	S11 (ang)	S21 (dB)	S21 (ang)	S12 (dB)	S12 (ang)	Gain (dB)	Phase (deg)
50	-18.23	174.74	19.89	177.21	-22.60	-0.68	17.21	-148.15
250	-18.28	162.59	19.75	165.56	-22.48	-0.53	17.25	-147.67
500	-17.36	147.85	19.50	151.86	-22.44	-0.61	17.21	-148.15
750	-18.86	130.86	19.09	138.79	-22.46	-1.53	19.11	-146.83
1000	-20.20	108.49	18.57	126.44	-22.42	-2.17	19.88	-144.23
1250	-21.82	84.57	18.05	114.78	-22.30	-3.17	20.88	-140.74
1500	-22.73	53.36	17.47	103.87	-22.14	-4.38	21.46	-137.74
1750	-22.84	27.48	16.86	93.52	-21.87	-5.46	21.98	-135.07
2000	-21.25	9.33	16.26	83.93	-21.75	-4.47	21.98	-135.07
2250	-18.04	-0.39	15.69	75.43	-21.40	-5.54	23.33	-129.08
2500	-18.33	-7.20	15.34	68.57	-20.82	-5.78	23.88	-126.98
2750	-19.57	-12.19	14.80	59.90	-20.29	-5.53	24.59	-124.37
3000	-21.03	-10.51	14.30	51.45	-19.75	-5.53	25.34	-121.54
3250	-23.01	-10.01	13.83	43.05	-19.21	-5.53	26.23	-118.27
3500	-24.57	13.25	13.33	34.97	-18.82	-16.08	27.07	-115.02
3750	-24.13	41.90	12.78	26.51	-19.65	-18.64	27.86	-111.52
4000	-21.65	64.98	12.28	18.62	-19.25	-22.08	28.79	-106.49
4250	-19.84	74.82	11.83	11.17	-19.17	-25.79	29.81	-100.24
4500	-18.66	82.81	11.40	4.20	-18.99	-28.99	30.96	-94.08
4750	-18.43	89.31	10.99	-3.54	-18.72	-31.96	32.34	-90.85
5000	-19.43	99.10	10.68	-10.20	-18.22	-35.34	33.86	-86.62
5250	-21.15	118.11	10.43	-16.78	-17.98	-37.98	35.54	-81.82
5500	-22.30	145.00	10.25	-23.41	-17.55	-40.47	38.47	-75.75
5750	-20.49	175.26	9.90	-30.29	-17.17	-44.86	41.86	-68.21
6000	-18.75	-172.37	9.57	-37.47	-16.67	-47.67	45.67	-60.32

Device S-parameters are available for download on the website at: <http://www.wj.com>

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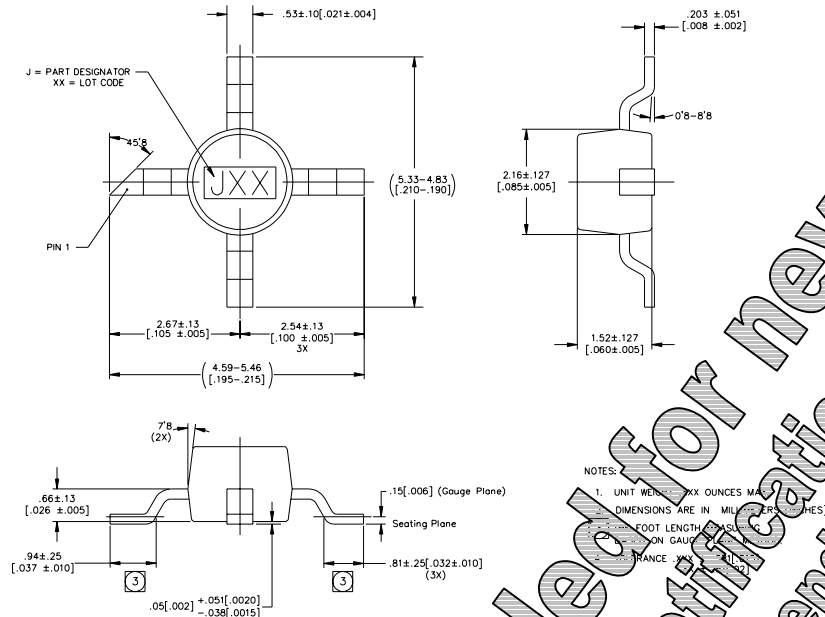
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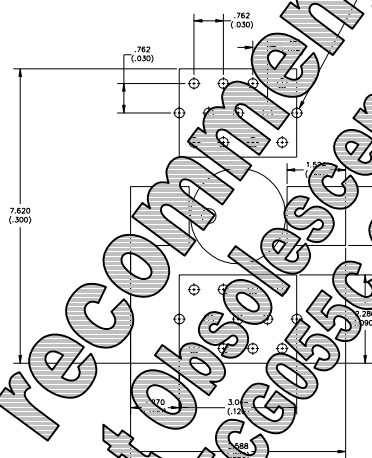
## AG603-86 (SOT-86 Package) Mechanical Information

This package may contain lead-bearing materials. The plating material on the leads is Sn.

### Outline Drawing



### Land Pattern



### Thermal Specifications

Parameter	Rating
Operating Case Temp.	-40 to +85 °C
Thermal Resistance, $\theta_{jc}$	16 °C/W
Junction Temperature, $T_{jc}$	165 °C

- The thermal resistance is referenced from the hottest part of the junction to the ground pad (pin 2 or 4).
- This corresponds to the typical biasing condition of +5.16V, 5 mA at 85 °C case temperature. A maximum MTTI of 5 million hours is achieved for junction temperatures below 177 °C.

### Product Marking

The component will be marked with a "J" designator followed by a two digit numeric code on the top surface of the package.

Use and reliability specifications for this part are located on the website in the "Application Note" section.

### MSL / ESD Rating



Caution! ESD sensitive device.

ESD Rating: Class 0  
 Value: Passes at 150 V  
 Test: Human Body Model (HBM)  
 Standard: JEDEC Standard JESD22-A114

ESD Rating: Class II  
 Value: Passes at 250 V  
 Test: Charged Device Model (CDM)  
 Standard: JEDEC Standard JESD22-C101

MSL Rating: Level 1  
 Standard: JEDEC Standard J-STD-020A

### Mounting Config. Notes

- Ground / thermal vias are critical for the proper performance of this device. Vias should use a .35mm (#80 / .0135") diameter drill and have a final plated thru diameter of .25 mm (.010").
- Add as much copper as possible to inner and outer layers near the part to ensure optimal thermal performance.
- Mounting screws can be added near the part to fasten the board to a heatsink. Ensure that the ground / thermal via region contacts the heatsink.
- Do not put solder mask on the backside of the PC board in the region where the board contacts the heatsink.
- RF trace width depends upon the PC board material and construction.
- Use 1 oz. Copper minimum.
- All dimensions are in millimeters (inches). Angles are in degrees.

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